

# N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY							
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)				
20	0.033 at V <sub>GS</sub> = 4.5 V	6.8	10 nC				
	0.045 at V <sub>GS</sub> = 2.5 V	6.8	TONC				

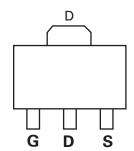
#### **FEATURES**

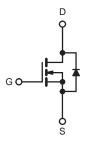
· DT-Trench Power MOSFET



#### **APPLICATIONS**

· Load Switches for Portable Devices





N-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	20	V		
Gate-Source Voltage	V <sub>GS</sub>	± 12	V		
	T <sub>C</sub> = 25 °C		6.8 <sup>a</sup>		
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 70 °C		6 <sup>a</sup>		
Continuous Brain Current (1) = 130 C)	T <sub>A</sub> = 25 °C	l <sub>D</sub>	6.8 <sup>a, b, c</sup>		
	T <sub>A</sub> = 70 °C		6 <sup>a, b, c</sup>	A	
Pulsed Drain Current		I <sub>DM</sub>	30		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	5.2 2.1 <sup>b, c</sup>		
Continuous Source-Diam Diode Current	T <sub>A</sub> = 25 °C	l 's			
	T <sub>C</sub> = 25 °C		6.3		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	P <sub>D</sub>	4	W	
Maximum Fower Dissipation	T <sub>A</sub> = 25 °C	1 'D	2.5 <sup>b, c</sup>	VV	
	T <sub>A</sub> = 70 °C		1.6 <sup>b, c</sup>		
Operating Junction and Storage Temperatur	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		
Soldering Recommendations (Peak Tempera	ature) <sup>e, f</sup>		260		

THERMAL RESISTANCE RATINGS								
Parameter	Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient <sup>a, c, d</sup>	t ≤ 5 s	R <sub>thJA</sub>	40	50	°C/W			
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	15	20	0/11			

- a. Package limited, T<sub>C</sub> = 25 °C.
  b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 95 °C/W.
- e. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	<u>.</u>				I.	•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	1 - 250		25			
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	$I_D = 250  \mu A$		- 4.0		mV/°C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	0.6		1.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zara Oata Valta va Daria Oamani	1 .	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	DSS	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 8.3 \text{ A}$		0.026	0.033	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 4.5 \text{ A}$		0.030	0.045		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_D = 8.3 \text{ A}$		45		S	
Dynamic <sup>b</sup>						1	
Input Capacitance	C <sub>iss</sub>			1200			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		220		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			100		1	
Total Cata Chausa	Q <sub>g</sub> -	$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 8.3 \text{ A}$		22	33	nC	
Total Gate Charge				10	15		
Gate-Source Charge		$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 8.3 \text{ A}$		2.5			
Gate-Drain Charge	$Q_{gd}$			1.7			
Gate Resistance	$R_g$	f = 1 MHz		2.4		Ω	
Turn-on Delay Time	t <sub>d(on)</sub>			15	25		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 1.5 $\Omega$		10	15	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong 6.7$ A, $V_{GEN}=4.5$ V, $R_g=1$ $\Omega$		35	55		
Fall Time	t <sub>f</sub>			12	20		
Turn-on Delay Time	t <sub>d(on)</sub>			10	15		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 1.5 $\Omega$		12	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong 6.7$ A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		25	40		
Fall Time	t <sub>f</sub>			10	15	1	
Drain-Source Body Diode Characteristic	s			•		•	
Continuous Source-Drain Diode Current	I <sub>S</sub>	$T_C = 25  ^{\circ}C$			5.2	^	
Pulse Diode Forward Current	I <sub>SM</sub>				30	A	
Body Diode Voltage	$V_{SD}$	$I_S = 6.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			20	40	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	L = 6.7 A dl/dt = 100 A/vo T = 25.00		10	20	nC	
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = 6.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		10			
Reverse Recovery Rise Time	t <sub>b</sub>			10		ns	

#### Notes:

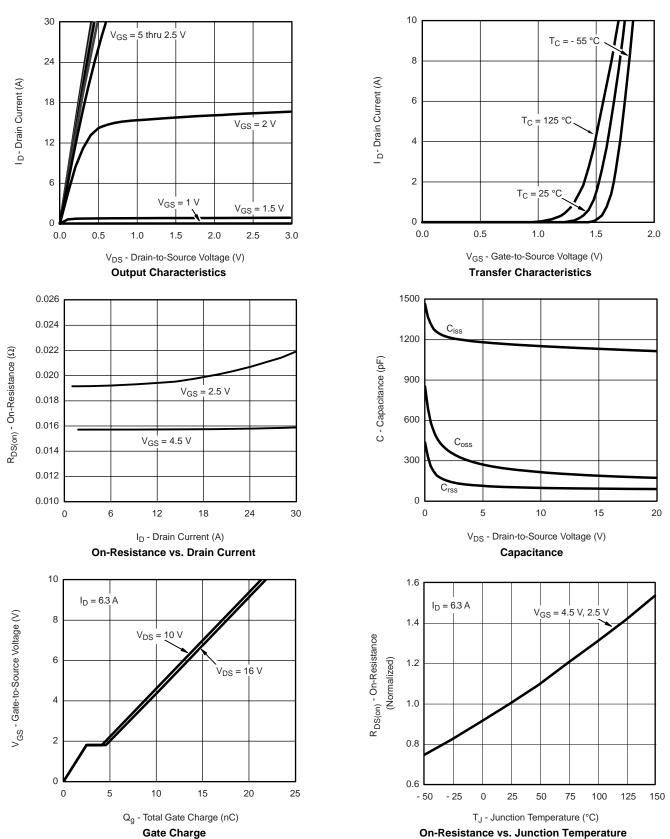
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

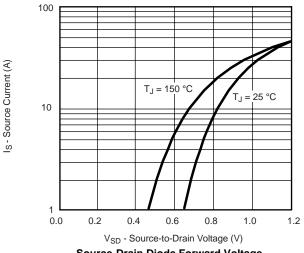




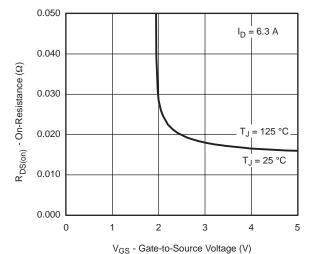


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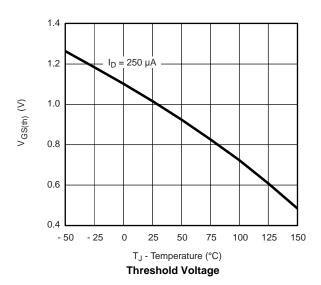
# www.din-tek.jp

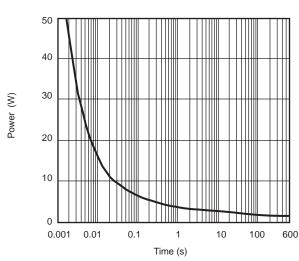


### Source-Drain Diode Forward Voltage

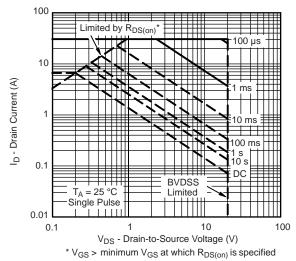


On-Resistance vs. Gate-to-Source Voltage





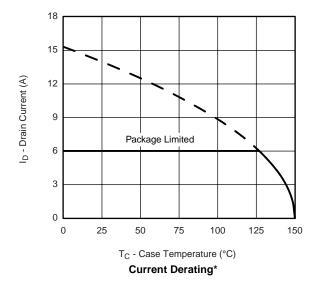
Single Pulse Power

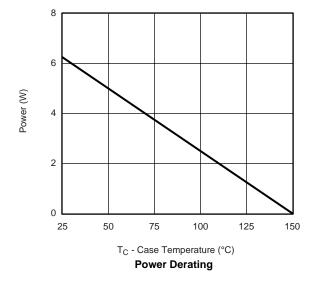


Safe Operating Area, Junction-to-Ambient



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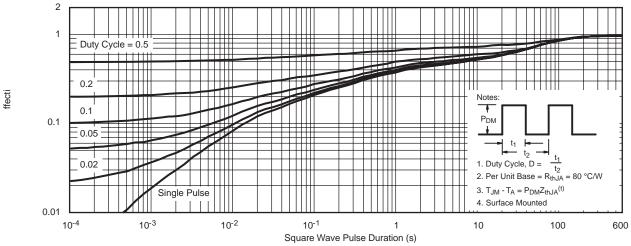




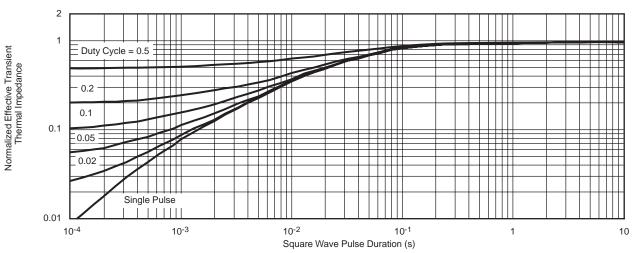
<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

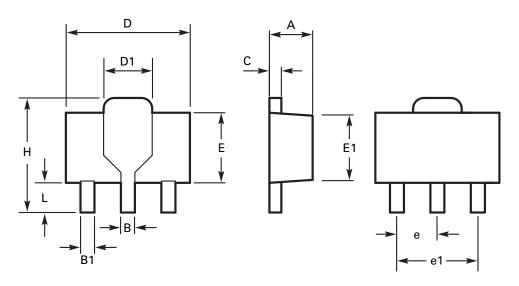


Normalized Thermal Transient Impedance, Junction-to-Foot





# Package outline - SOT89



DIM	Millin	neters	Inches DIM Millimeters Incl		Millimeters		hes		
	Min	Max	Min	Max		Min	Max	Min	Max
Α	1.40	1.60	0.550	0.630	Е	2.29	2.60	0.090	0.102
В	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	е	1.50 BSC		0.059 BSC	
С	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	Н	3.94	4.25	0.155	0.167
D1	1.62	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches





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